

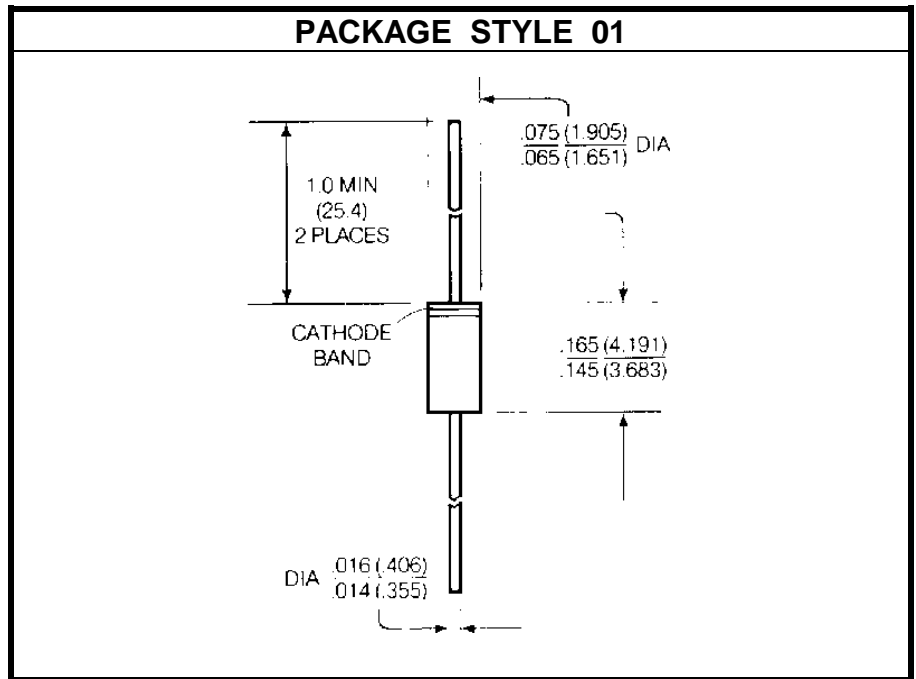
SILICON PIN DIODE

DESCRIPTION:

The **AP3000C-11** is a Passivated Epitaxial Silicon PIN Diode Housed in a Hermetically Sealed Glass Package. This Device is Designed to Cover a Wide Range of control Applications Such as RF Switching, Phase Shifting, Modulation, Duplexing Limiting and Pulse Forming.

MAXIMUM RATINGS

I_C	100 mA
V_{CE}	300 V
P_{DISS}	250 mW @ T _A = 25 °C
T_J	-65 °C to +175 °C
T_{STG}	-65 °C to +175 °C
θ_{JC}	20 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_B	I _R = 10 μA	300			V
C_J	V _R = 50 V V _R = 40 V			0.2	pF
C_P			0.10		pF
L_S			1.0		nH
R_S	I _F = 50 mA			0.6	Ohms
T_L	I _F = 10 mA I _R = 6.0 mA		1000		nS
T_{rr}	I _F = 20 mA I _R = 100 mA @ 90%		100		nS
I-REGION			30		μM